FH2311A

P-Channel Enhancement Mode MOSFET

Description

The FH2311A uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as -2.5V. This device is suitable for use as a wide variety of applications.

Applications

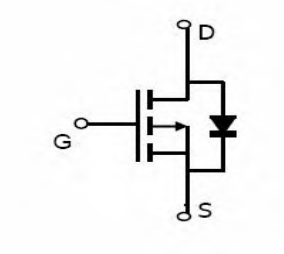
- PWM Applications
- Load Switch
- Power Management

Features

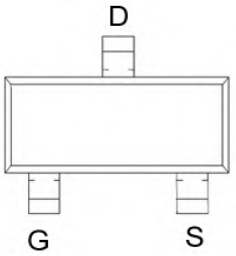
- V_{DS} = - 17V ; I_D = -9.0A

  $R_{DS(ON)}$ (Typ.)= 16 mΩ @V_{GS} = -4.5V

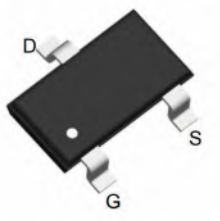
  $R_{DS(ON)}$ (Typ.)= 23 mΩ @V_{GS} = -2.5V
- Low Gate Charge
- High Power and current handing capability
- Lead free product is acquired
- SMD Package(SOT-23)



Schematic diagram



Marking and Pin Assignment



SOT-23 top view

Table 1. Absolute Maximum Ratings (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage (V_{GS}=0V)	-17	V
V_{GS}	Gate-Source Voltage (V_{DS}=0V)	±12	V
I_D	Drain Current-Continuous(T_A=25℃)	-9	A
	Drain Current-Continuous(T_A=100℃)	-5.8	A
$I_{DM\ (pluse)}$	Drain Current-Continuous@ Current-Pulsed (Note 1)	-36	A
P_D	Maximum Power Dissipation(T_A=25℃)	1.25	W
	Maximum Power Dissipation(T_A=100℃)	0.6	W
E_{AS}	Avalanche energy (Note 2)	20	mJ
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	℃

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction-to- Ambient		102	℃/W

Table 3. Electrical Characteristics (T_J=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V I_D=-250μA	-17			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-17V, V_{GS}=0V T_J=25℃			-1	μA
		V_{DS}=-17V, V_{GS}=0V T_J=125℃			-100	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±12V, V_{DS}=0V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=-250μA	-0.5		-1	V
g_{FS}	Forward Transconductance	V_{DS}=-5V, I_D=-10A		16.6		S
$R_{DS(ON)}$	Drain-Source On-State Resistance	V_{GS}=-4.5V, I_D=-5A T_J=25℃		16	21	mΩ
$R_{DS(ON)}$	Drain-Source On-State Resistance	V_{GS}=-2.5V, I_D=-4A T_J=25℃		23	28	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=-10V,V_{GS}=0V, f=1.0MHz		1440		pF
C_{oss}	Output Capacitance			294		pF
C_{rss}	Reverse Transfer Capacitance			242		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1.0MHz		25		Ω
Switching Parameters						
$t_{d(on)}$	Turn-on Delay Time	V_{GS}=-10V, V_{DS}=-6V, R_L=2Ω, R_{GEN}=3Ω		14.4		nS
t_r	Turn-on Rise Time			5.5		nS
$t_{d(off)}$	Turn-Off Delay Time			59.4		nS
t_f	Turn-Off Fall Time			21.6		nS
Q_g	Total Gate Charge	V_{GS}=-4.5V, V_{DS}=-6V, I_D=-5A		20		nC
Q_{gs}	Gate-Source Charge			5		nC
Q_{gd}	Gate-Drain Charge			6		nC
Source-Drain Diode Characteristics						
I_{SD}	Source-Drain Current (Body Diode)				-9	A
V_{SD}	Forward on Voltage (Note 3)	V_{GS}=0V, I_S=-5A			-1.2	V
t_{rr}	Reverse Recovery Time	I_F=-5A, dI/dt=-100A/μs		31.2		ns
Q_{rr}	Reverse Recovery Charge	I_F=-5A, dI/dt=-100A/μs		10.9		nC

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.
Notes 2.E_{AS} condition: T_J=25℃,V_{DD}=-20V,V_G=-10V, Rg=25Ω, L=0.5mH.
Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.

Typical Electrical And Thermal Characteristics (Curves)

Figure 1. Output Characteristics

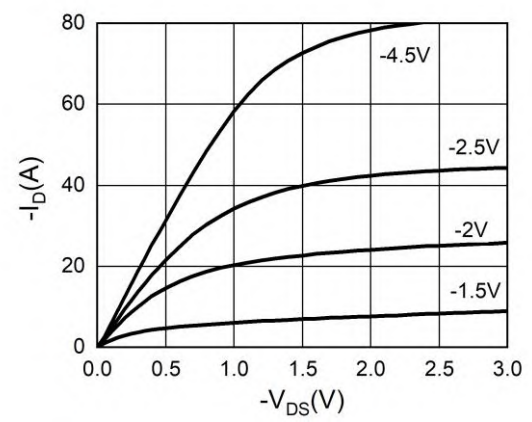


Figure 2. Transfer Characteristics

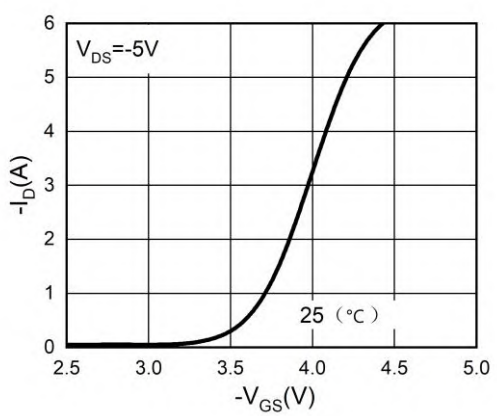


Figure 3. Power Dissipation

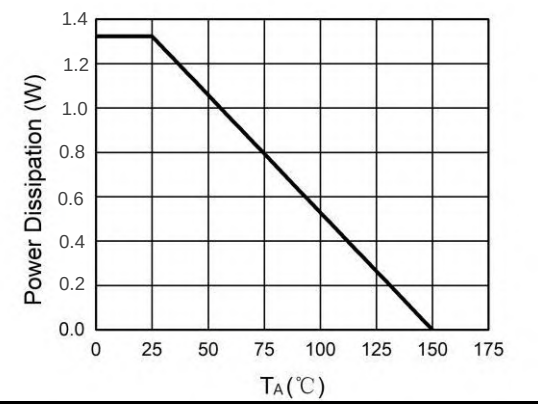


Figure 4. Drain Current

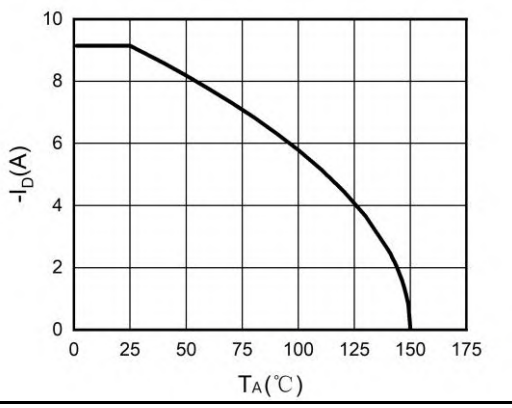


Figure 5. BV_{DSS} vs Junction Temperature

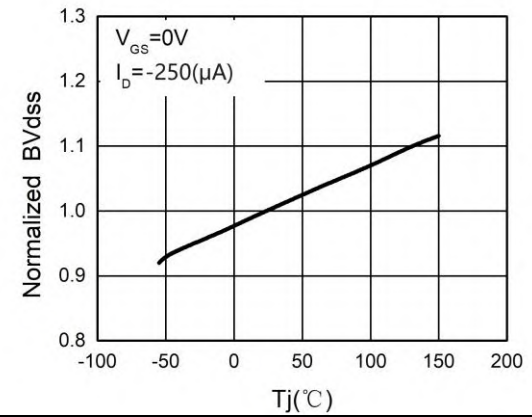
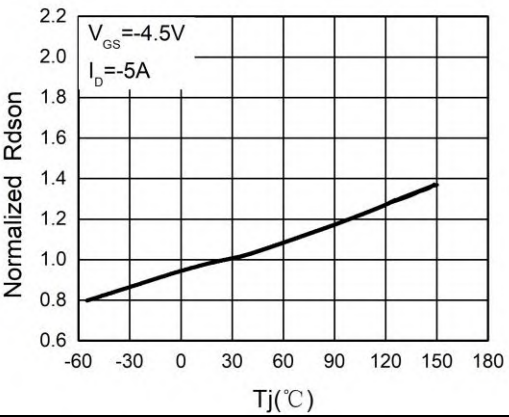


Figure 6. $R_{DS(ON)}$ vs Junction Temperature



Typical Electrical And Thermal Characteristics (Curves)

Figure 7. Gate Charge Waveforms

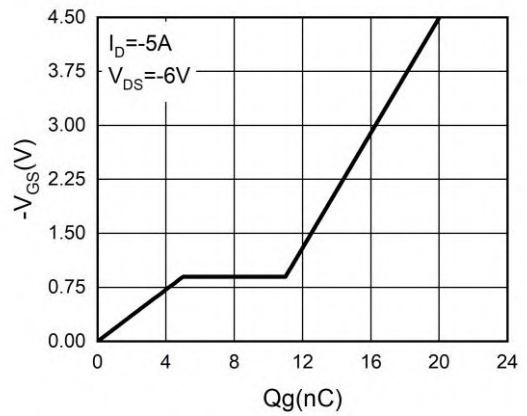


Figure 8. Capacitance

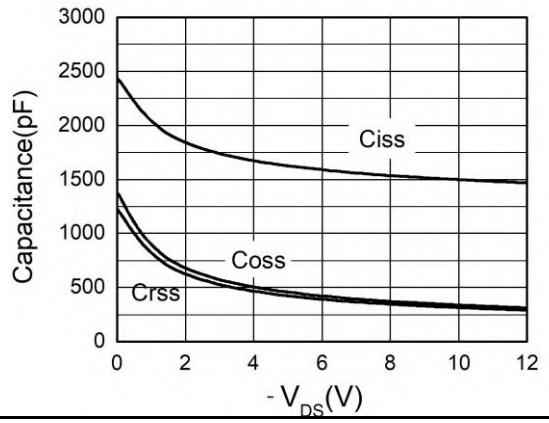


Figure 9. Body-Diode Characteristics

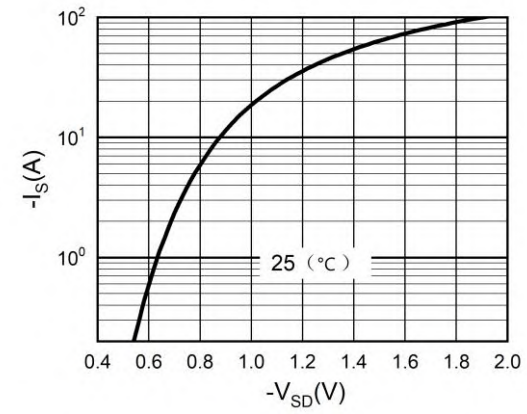
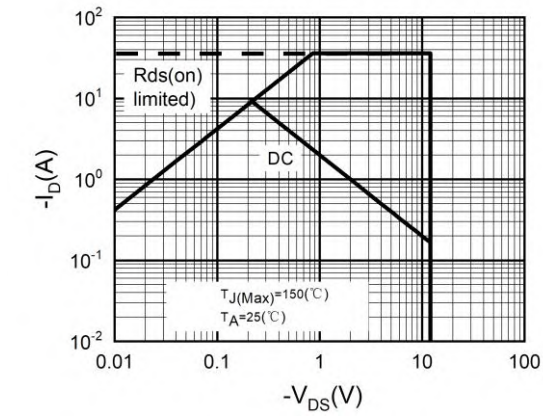
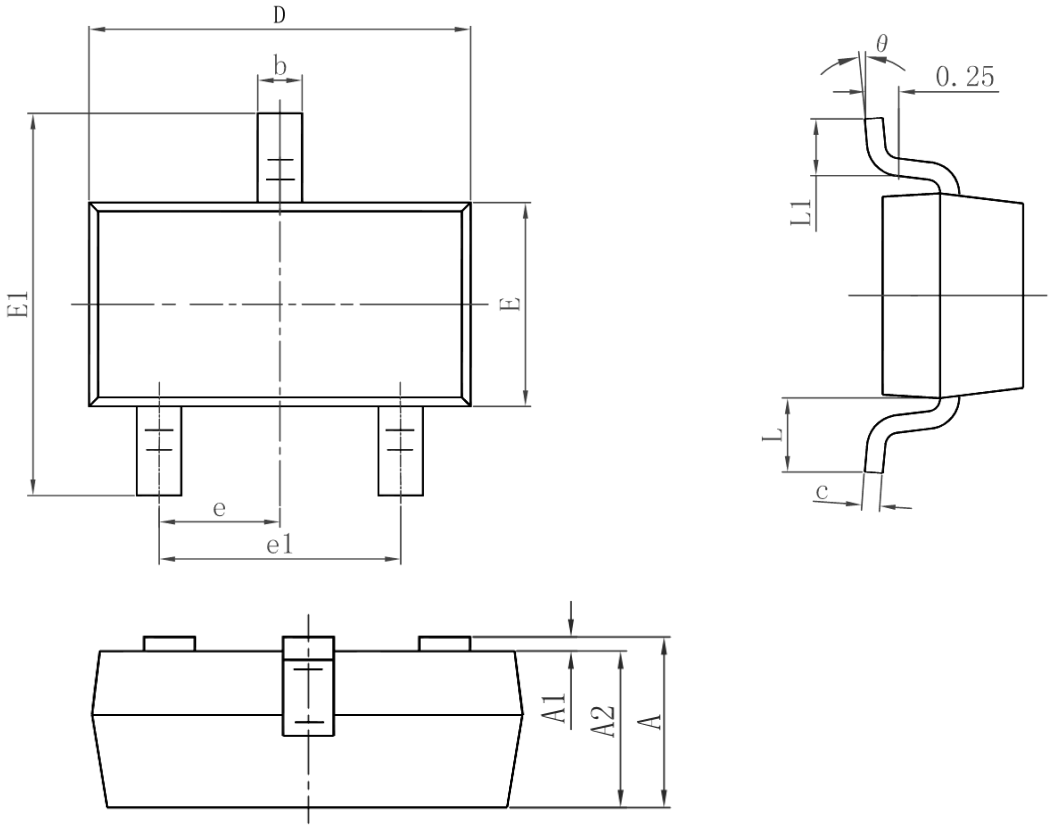


Figure 10. Maximum Safe Operating Area



Package Dimensions : SOT-23



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°